Filing Date: August 31, 2000

Title: CONTAINER CAPACITOR STRUCTURE AND METHOD OF FORMATION THEREOF

providing an insulating layer around an exterior surface of the cup-shaped bottom electrode, such that an entire vertical height of the exterior surface is in contact with the insulating layer;

masking a first portion of the insulating layer;

etching a second portion of the insulating layer from a first region of the exterior surface to expose the first region of the exterior surface, such that the insulating layer remains in contact with an entire vertical height of a remaining region of the exterior surface;

depositing a dielectric layer on the first region of the exterior surface; and depositing a conductive layer on the dielectric layer.

#### **REMARKS**

Applicant has amended claims 29 and 67. Claims 29 and 67 remain for consideration in this application.

## Rejection Under U.S.C. § 103

Claims 29 and 67 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Dennison (U. S. Patent No. 5,362,666).

Referring to claim 29, the claim as amended recites, in part, "masking a first partial circumferential portion of said insulating layer." This process of masking and the subsequently recited etching is neither taught nor disclosed in Dennison, as Dennison performs an etch to remove the supporting insulator 32 to a uniform depth for the entire circumference of the container. (See Figs. 4-5 and col. 10).

Referring to claim 67, the claim as amended recites, in part, "etching a second portion of the insulating layer from a first region of the exterior surface to expose the first region of the exterior surface, such that the insulating layer remains in contact with an entire vertical height of a remaining region of the exterior surface." This is clearly distinguished from the structure of Dennison which exposes at least a part of the exterior vertical surface of the bottom electrode for the entire bottom electrode.

AMENDMENT AND RESPONSE

Serial Number: 09/652,999 Filing Date: August 31, 2000

Title: CONTAINER CAPACITOR STRUCTURE AND METHOD OF FORMATION THEREOF

#### **CONCLUSION**

In view of the above amendments and remarks, Applicant respectfully submits that all claims are in condition for allowance and requests reconsideration of the application and allowance of claims. The Examiner is invited to contact Applicant's attorney to discuss any questions that may remain with respect to the present application.

Respectfully submitted,

Durcan et al.

By their Representatives,

Fogg Slifer Polglaze Leffert & Jay, P.A.

Page 3

Docket No. 400.153US03

P.O. Box 581009

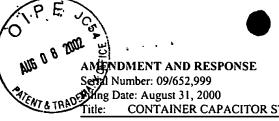
Minneapolis, MN 55458-1009

(612) 312-2202

Date 8 August 2002

Daniel J. Polglaze

Reg. No. 39,801



Appendix: Page1 Docket No. 400.153US03

CONTAINER CAPACITOR STRUCTURE AND METHOD OF FORMATION THEREOF

## **MARKED-UP VERSION OF AMENDMENTS**

# **IN THE CLAIMS**

29. (Amended) A method for forming a container capacitor, comprising the steps of: providing a cup-shaped bottom electrode;

providing an insulating layer around and in contact with an exterior surface of said cupshaped bottom electrode;

masking a first partial circumferential portion of said insulating layer;

etching a second portion of said insulating layer from a <u>second partial circumferential</u> part of said exterior surface to expose the part of said exterior surface;

depositing a dielectric layer on said part of said exterior surface; and depositing a conductive layer on said dielectric layer.

RECEIVED

AUG 1 4 2002

Technology Center 2600

67. (Amended) A method for forming a container capacitor comprising: fabricating a cup-shaped bottom electrode;

providing an insulating layer around an exterior surface of the cup-shaped bottom electrode, such that an entire vertical height of the exterior surface is in contact with the insulating layer;

masking a first portion of the insulating layer;

etching a second portion of the insulating layer from a first region of the exterior surface to expose the first region of the exterior surface, such that the insulating layer remains in contact with an entire vertical height of a remaining region of the exterior surface;

depositing a dielectric layer on the first region of the exterior surface; and depositing a conductive layer on the dielectric layer.

AUG 19 ZIIIZ
TECHNOLOGY CENTER 2800